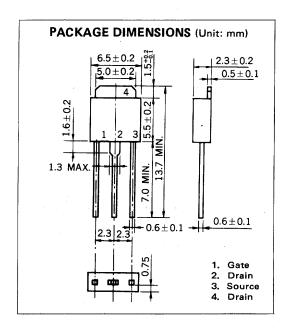


# MOS FIELD EFFECT POWER TRANSISTOR **2SJ128**

# **FAST SWITCHING** P-CHANNEL SILICON POWER MOS FET **INDUSTRIAL USE**



## **FEATURES**

- Suitable for switching power supplies, actuater controls, and pulse circuits.
- Low R<sub>DS(on)</sub>
- No second breakdown
- 4 V Gate Drive Logic level —

# ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

| Drain to Source Voltage  | $V_{DSS}$               | -100        | V   |
|--------------------------|-------------------------|-------------|-----|
| Gate to Source Voltage   | $V_{GSS}$               | ∓20         | ٧   |
| Continuous Drain Current | I <sub>D(DC)</sub>      | ∓2          | Α   |
| Peak Drain Current       | I <sub>D(pulse)</sub> * | ∓8          | . A |
| Total Power Dissipation  | $P_T$                   | 20          | W   |
| Channel Temperature      | $T_ch$                  | 150         | °C  |
| Storage Temperature      | $T_{stg}$               | -55 to +150 | °C  |

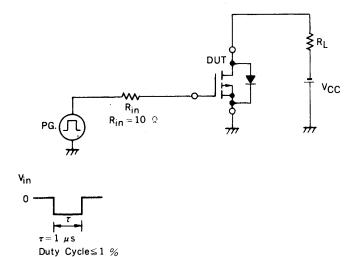
<sup>\*</sup> PW  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  10 %

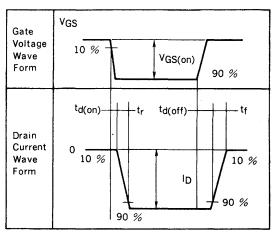
## **ELECTRICAL CHARACTERISTICS (TA = 25 °C)**

| CHARACTERISTIC                      | SYMBOL               | MIN. | TYP. | MAX. | UNIT | TEST CONDITIONS                                                                |  |
|-------------------------------------|----------------------|------|------|------|------|--------------------------------------------------------------------------------|--|
| Drain Leakage Current               | <sup>1</sup> DSS     |      |      | -10  | μΑ   | V <sub>DS</sub> = -100 V, V <sub>GS</sub> = 0                                  |  |
| Gate to Source Leakage Current      | 1 <sub>GSS</sub>     |      |      | ∓100 | nA   | V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0                                   |  |
| Gate to Source Cutoff Voltage       | V <sub>GS(off)</sub> | -1.0 |      | -3.0 | V    | V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA                                |  |
| Forward Transfer Admittance         | lyfsl                | 1.0  |      |      | S    | V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 A                                 |  |
| Drain to Source On-State Resistance | R <sub>DS</sub> (on) |      | 0.8  | 1.0  | Ω    | V <sub>GS</sub> = -10 V, I <sub>D</sub> = -1 A                                 |  |
| Drain to Source On-State Resistance | R <sub>DS(on)</sub>  |      | 1.1  | 1.5  | Ω    | V <sub>GS</sub> = -4 V, I <sub>D</sub> = -0.8 A                                |  |
| Input Capacitance                   | C <sub>iss</sub>     |      | 1000 |      | pF   | V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0<br>f = 1 MHz                      |  |
| Output Capacitance                  | Coss                 |      | 200  |      | pF   |                                                                                |  |
| Reverse Transfer Capacitance        | C <sub>rss</sub> .   |      | 25   |      | pF   |                                                                                |  |
| Turn-On Delay Time                  | td(on)               | ·    | 30   |      | ns   | I <sub>D</sub> = −1 A, V <sub>CC</sub> = −50 V<br>V <sub>GS</sub> (on) = −10 V |  |
| Rise Time                           | t <sub>r</sub>       |      | 30   |      | ns   |                                                                                |  |
| Turn-Off Delay Time                 | <sup>t</sup> d(off)  |      | 110  |      | ns   | $R_{L} = 10 \Omega$ $R_{in} = 10 \Omega$                                       |  |
| Fall Time                           | .t <sub>f</sub>      |      | 40   |      | ns   |                                                                                |  |

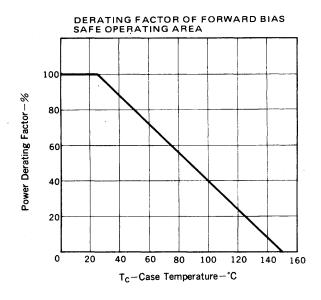
Printed in Japan

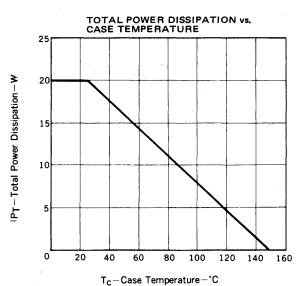
## **TURN-ON AND TURN-OFF TIME TEST CIRCUIT**

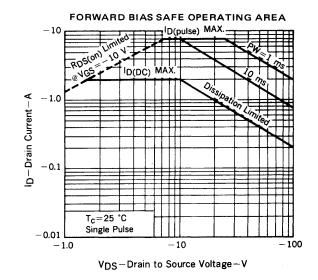


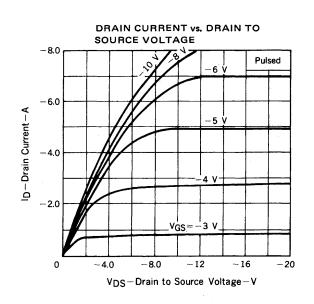


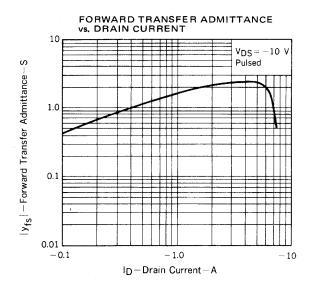
# TYPICAL CHARACTERISTICS (TA = 25 °C)

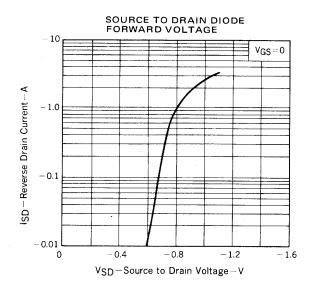


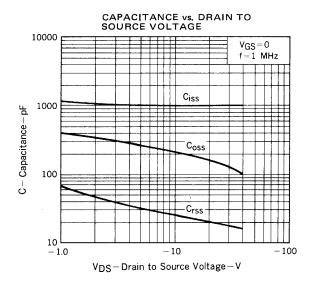


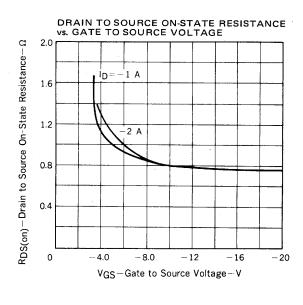


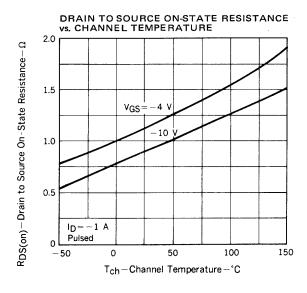


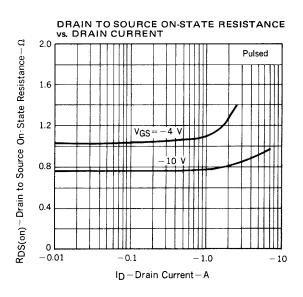


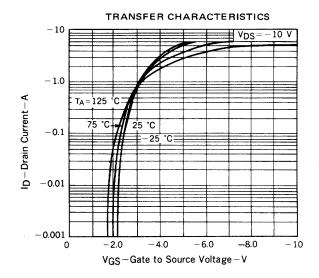


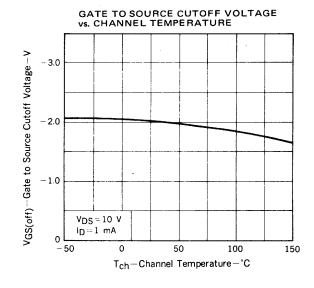


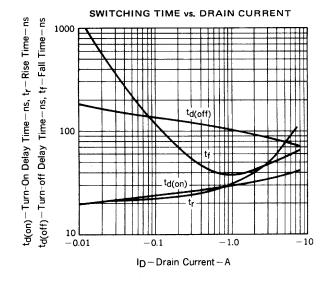












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Anti-radioactive design is not implemented in this product.

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